

**XPT IGBT**

$V_{CES} = 1200V$

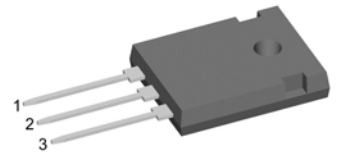
$I_{C25} = 38A$

$V_{CE(sat)} = 1.8V$

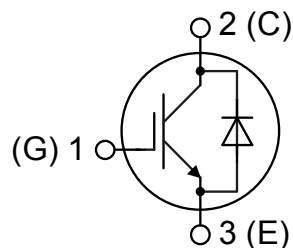
Copack

Part number

IXA20IF1200HB



Backside: collector

**Features / Advantages:**

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
  - short circuit rated for 10  $\mu$ sec.
  - very low gate charge
  - low EMI
  - square RBSOA @ 3x  $I_c$
- Thin wafer technology combined with the XPT design results in a competitive low  $V_{CE(sat)}$
- SONIC™ diode
  - fast and soft reverse recovery
  - low operating forward voltage

**Applications:**

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies
- Inductive heating, cookers
- Pumps, Fans

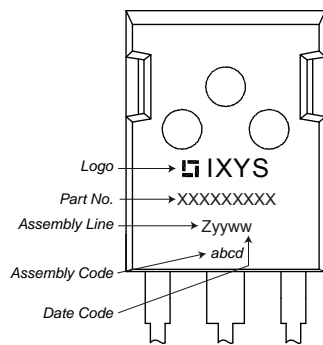
**Package: TO-247**

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

IGBT				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$V_{CES}$	collector emitter voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
$V_{GES}$	max. DC gate voltage				$\pm 20$	V	
$V_{GEM}$	max. transient gate emitter voltage				$\pm 30$	V	
$I_{C25}$	collector current	$T_C = 25^{\circ}C$			38	A	
$I_{C80}$		$T_C = 80^{\circ}C$			22	A	
$P_{tot}$	total power dissipation	$T_C = 25^{\circ}C$			165	W	
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 15A; V_{GE} = 15V$		1.8	2.1	V	
				2.1		V	
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.6mA; V_{GE} = V_{CE}$	5.4	5.9	6.5	V	
$I_{CES}$	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0V$			0.1	mA	
				0.1		mA	
$I_{GES}$	gate emitter leakage current	$V_{GE} = \pm 20V$			500	nA	
$Q_{G(on)}$	total gate charge	$V_{CE} = 600V; V_{GE} = 15V; I_C = 15A$		47		nC	
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600V; I_C = 15A$ $V_{GE} = \pm 15V; R_G = 56\Omega$		70		ns	
$t_r$	current rise time		$T_{VJ} = 125^{\circ}C$	40		ns	
$t_{d(off)}$	turn-off delay time		250		ns		
$t_f$	current fall time		100		ns		
$E_{on}$	turn-on energy per pulse		1.55		mJ		
$E_{off}$	turn-off energy per pulse		1.7		mJ		
<b>RBSOA</b>	reverse bias safe operating area	$V_{GE} = \pm 15V; R_G = 56\Omega$					
$I_{CM}$		$V_{CEmax} = 1200V$			45	A	
<b>SCSOA</b>	short circuit safe operating area	$V_{CEmax} = 900V$					
$t_{sc}$	short circuit duration	$V_{CE} = 900V; V_{GE} = \pm 15V$			10	$\mu s$	
$I_{sc}$	short circuit current	$R_G = 56\Omega; \text{non-repetitive}$		60		A	
$R_{thJC}$	thermal resistance junction to case				0.76	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.25		K/W	
<b>Diode</b>							
$V_{RRM}$	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
$I_{F25}$	forward current	$T_C = 25^{\circ}C$			45	A	
$I_{F80}$		$T_C = 80^{\circ}C$			24	A	
$V_F$	forward voltage	$I_F = 20A$			2.20	V	
				1.95		V	
$I_R$	reverse current	$V_R = V_{RRM}$			*	mA	
	* not applicable, see Ices value above				*	mA	
$Q_{rr}$	reverse recovery charge	$V_R = 600V$ $-di_F/dt = -400A/\mu s$ $I_F = 20A; V_{GE} = 0V$		3		$\mu C$	
$I_{RM}$	max. reverse recovery current		$T_{VJ} = 125^{\circ}C$	20		A	
$t_{rr}$	reverse recovery time		350		ns		
$E_{rec}$	reverse recovery energy		0.7		mJ		
$R_{thJC}$	thermal resistance junction to case				0.9	K/W	
$R_{thCH}$	thermal resistance case to heatsink			0.25		K/W	

Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			70	A
$T_{VJ}$	virtual junction temperature		-40		150	°C
$T_{op}$	operation temperature		-40		125	°C
$T_{stg}$	storage temperature		-40		150	°C
<b>Weight</b>				6		g
$M_D$	mounting torque		0.8		1.2	Nm
$F_C$	mounting force with clip		20		120	N

### Product Marking



### Part number

I = IGBT  
 X = XPT IGBT  
 A = Gen 1 / std  
 20 = Current Rating [A]  
 IF = Copack  
 1200 = Reverse Voltage [V]  
 HB = TO-247AD (3)

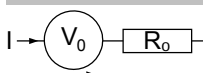
Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	IXA20IF1200HB	IXA20IF1200HB	Tube	30	508460

Similar Part	Package	Voltage class
IXA20I1200PB	TO-220AB (3)	1200

### Equivalent Circuits for Simulation

\* on die level

$T_{VJ} = 150\text{ °C}$

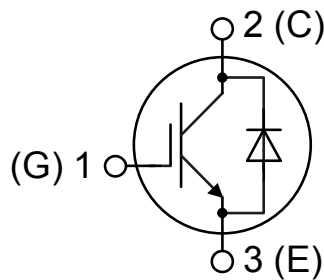
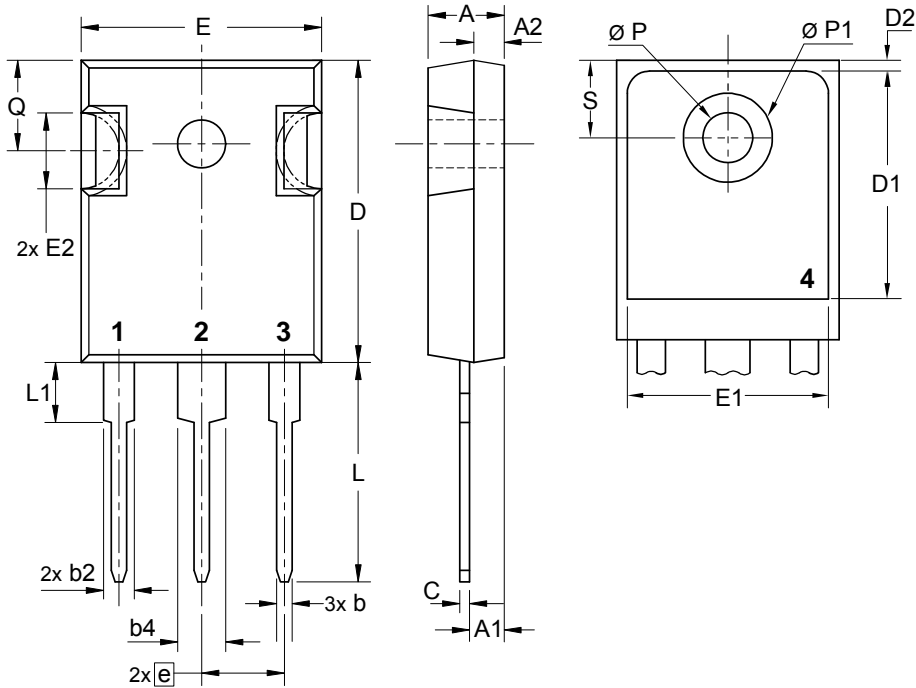


$V_{0\ max}$  threshold voltage

$R_{0\ max}$  slope resistance \*

	IGBT	Diode	
$V_{0\ max}$	1.1	1.25	V
$R_{0\ max}$	86	42.5	mΩ

## Outlines TO-247



**IGBT**

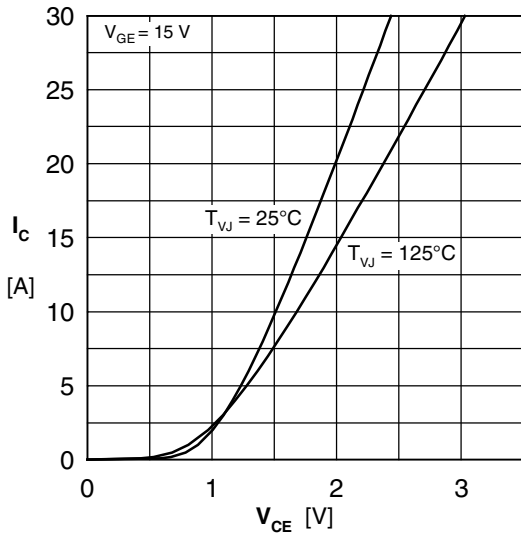


Fig. 1 Typ. output characteristics

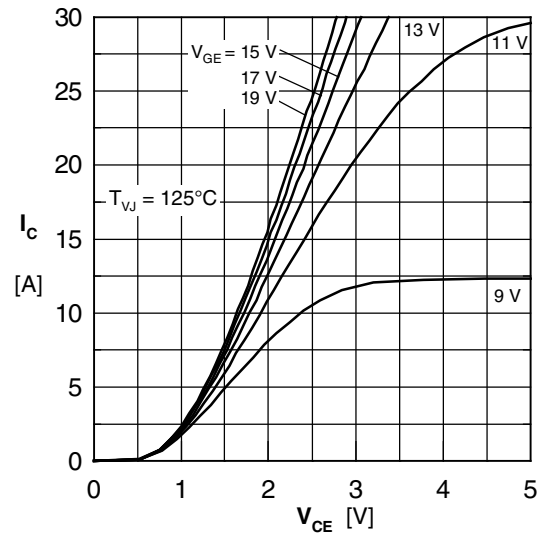


Fig. 2 Typ. output characteristics

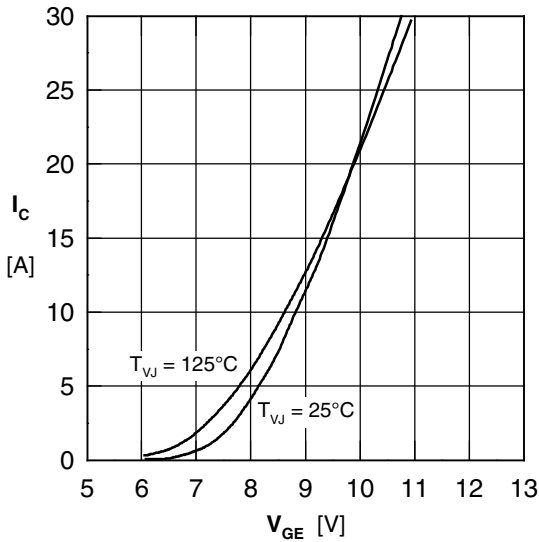


Fig. 3 Typ. transfer characteristics

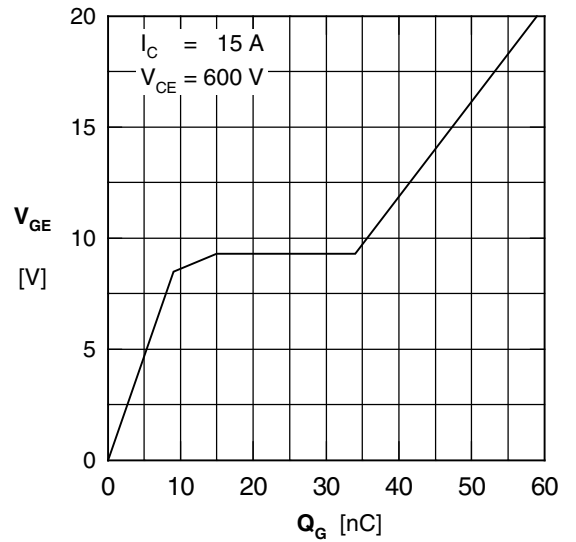


Fig. 4 Typ. turn-on gate charge

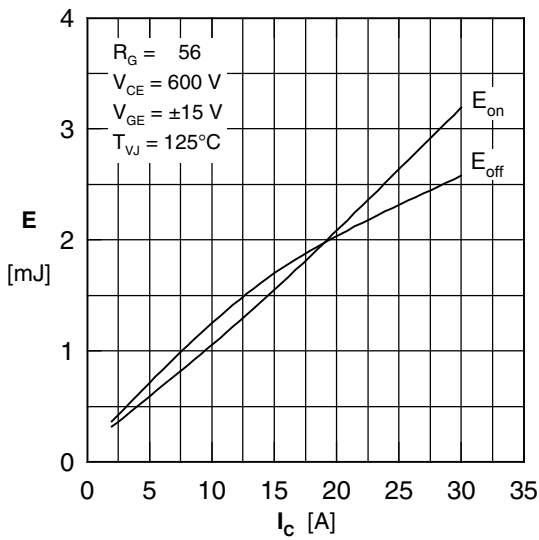


Fig. 5 Typ. switching energy vs. collector current

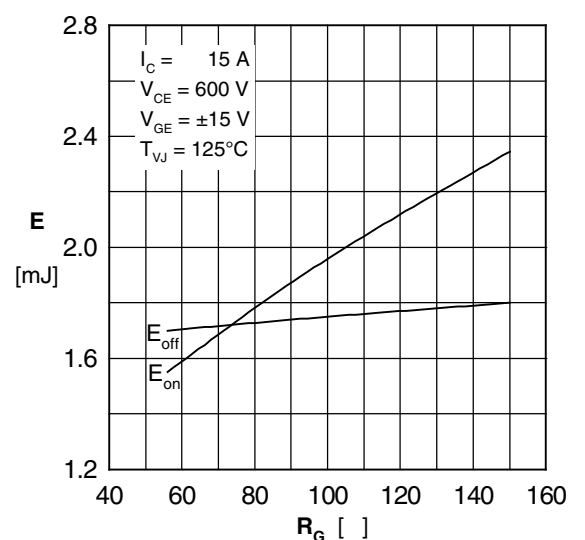


Fig. 6 Typ. switching energy vs. gate resistance

## Diode

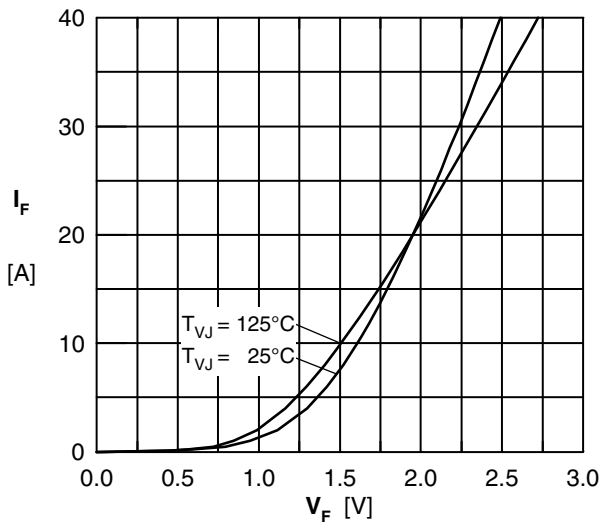


Fig. 7 Typ. Forward current versus  $V_F$

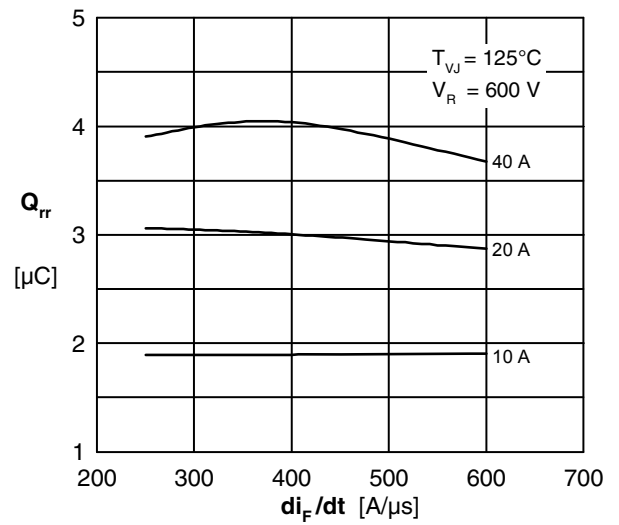


Fig. 8 Typ. reverse recov. charge  $Q_{rr}$  vs.  $di/dt$

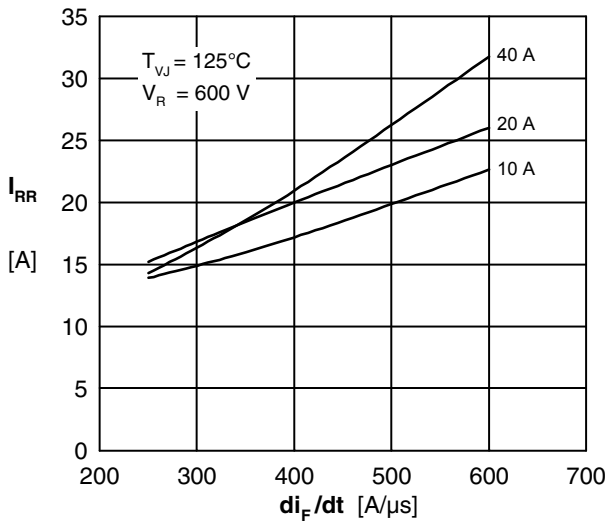


Fig. 9 Typ. peak reverse current  $I_{RM}$  vs.  $di/dt$

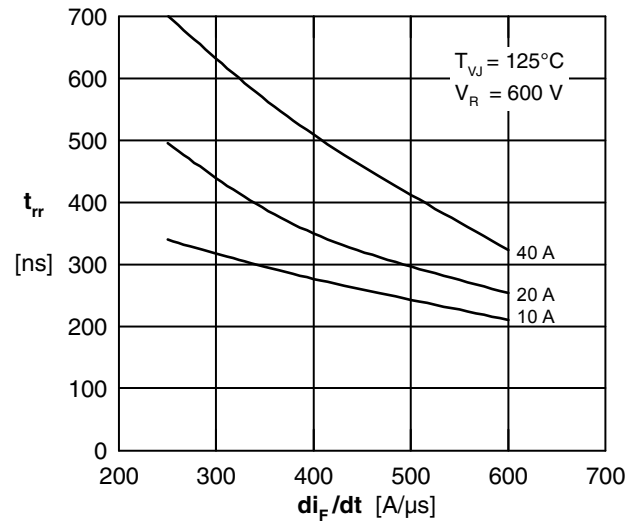


Fig. 10 Typ. recovery time  $t_{rr}$  versus  $di/dt$

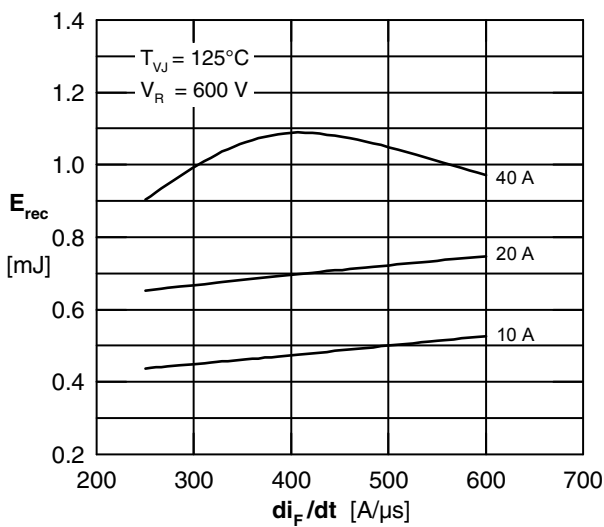


Fig. 11 Typ. recovery energy  $E_{rec}$  versus  $di/dt$

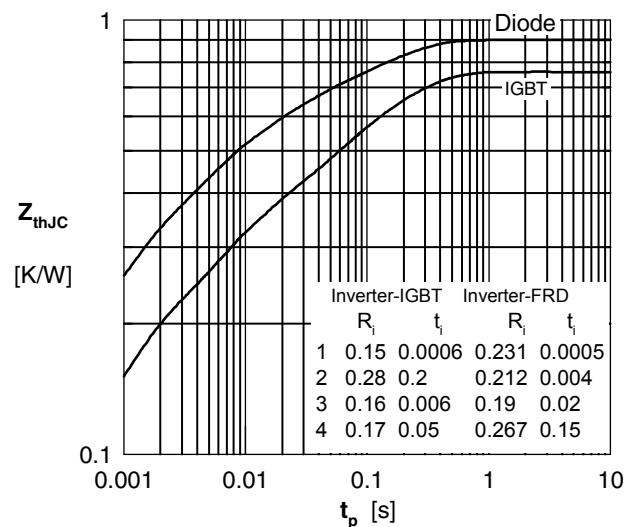


Fig. 12 Typ. transient thermal impedance



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